



Advanced Power
Electronics Corp.

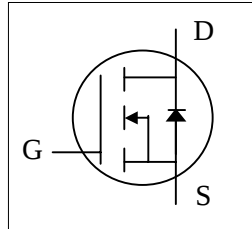
AP10N70R/P-A

Pb Free Plating Product

N-CHANNEL ENHANCEMENT MODE

POWER MOSFET

- ▼ 100% Avalanche Rated Test
- ▼ Fast Switching Performance
- ▼ Simple Drive Requirement
- ▼ RoHS Compliant

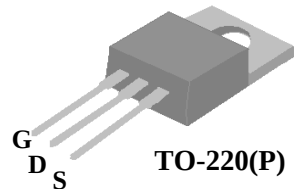
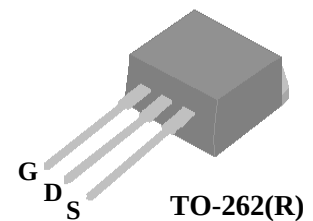


BV_{DSS}	650V
$R_{DS(ON)}$	0.6 Ω
I_D	10A

Description

AP10N70 series are specially designed as main switching devices for universal 90~265VAC off-line AC/DC converter applications. Both TO-220 and TO-262 type provide high blocking voltage to overcome voltage surge and sag in the toughest power system with the best combination of fast switching, ruggedized design and cost-effectiveness.

The TO-220 and TO-262 package is universally preferred for all commercial-industrial applications. The device is suited for switch mode power supplies, DC-AC converters and high current high speed switching circuits.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	± 30	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, V_{GS} @ 10V	10	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, V_{GS} @ 10V	6.8	A
I_{DM}	Pulsed Drain Current ¹	40	A
$P_D@T_C=25^\circ C$	Total Power Dissipation	174	W
	Linear Derating Factor	1.39	W/ $^\circ C$
E_{AS}	Single Pulse Avalanche Energy ²	50	mJ
I_{AR}	Avalanche Current	10	A
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Value	Unit
R_{thj-c}	Thermal Resistance Junction-case Max.	0.72	$^\circ C/W$
R_{thj-a}	Thermal Resistance Junction-ambient Max.	62	$^\circ C/W$

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =1.0mA	650	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =5.0A	-	-	0.6	Ω
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	2	-	4	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =5A	5	-	-	S
I _{DSS}	Drain-Source Leakage Current (T _j =25°C)	V _{DS} =600V, V _{GS} =0V	-	-	10	μA
	Drain-Source Leakage Current (T _j =150°C)	V _{DS} =480V, V _{GS} =0V	-	-	100	μA
I _{GSS}	Gate-Source Leakage	V _{GS} = ± 30V	-	-	±100	nA
Q _g	Total Gate Charge ³	I _D =10A	-	35.9	57	nC
Q _{gs}	Gate-Source Charge	V _{DS} =480V	-	8.3	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =10V	-	11.5	-	nC
t _{d(on)}	Turn-on Delay Time ³	V _{DD} =300V	-	14.9	-	ns
t _r	Rise Time	I _D =10A	-	19.7	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =10Ω, V _{GS} =10V	-	51.7	-	ns
t _f	Fall Time	R _D =30Ω	-	23.3	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	1950	3120	pF
C _{oss}	Output Capacitance	V _{DS} =15V	-	630	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	20	-	pF
R _g	Gate Resistance	f=1.0MHz	-	2	3	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ³	T _j =25°C, I _S =10A, V _{GS} =0V	-	-	1.5	V
t _{rr}	Reverse Recovery Time ²	I _S =10A, V _{GS} =0V,	-	640	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	7460	-	nC

Notes:

- 1.Pulse width limited by safe operating area.
- 2.Starting T_j=25°C, V_{DD}=50V, L=1.0mH, R_G=25Ω, I_{AS}=10A.
- 3.Pulse width ≤300us, duty cycle ≤2%.

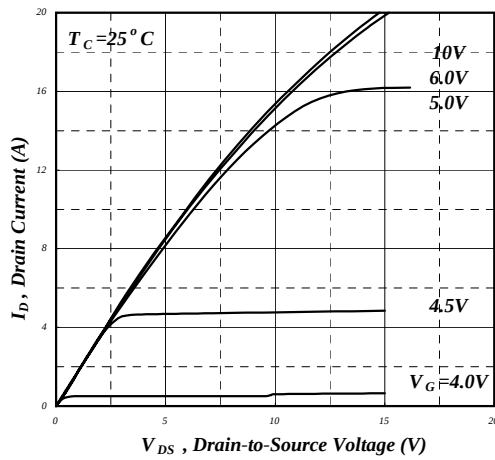


Fig 1. Typical Output Characteristics

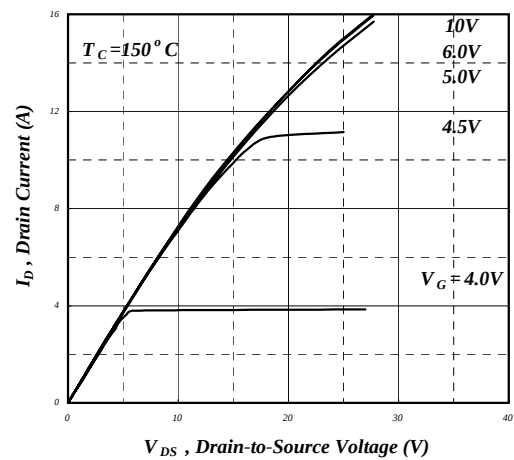


Fig 2. Typical Output Characteristics

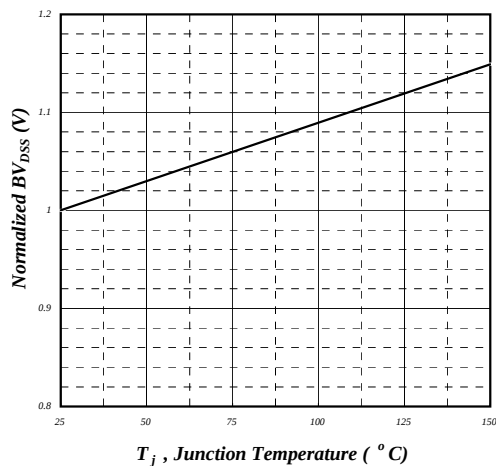


Fig 3. Normalized BV_{DSS} v.s. Junction Temperature

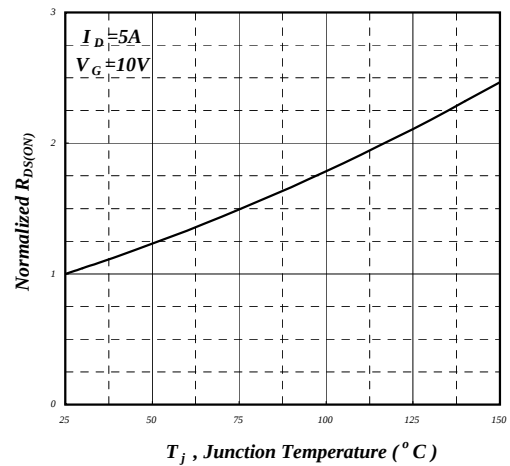


Fig 4. Normalized On-Resistance v.s. Junction Temperature

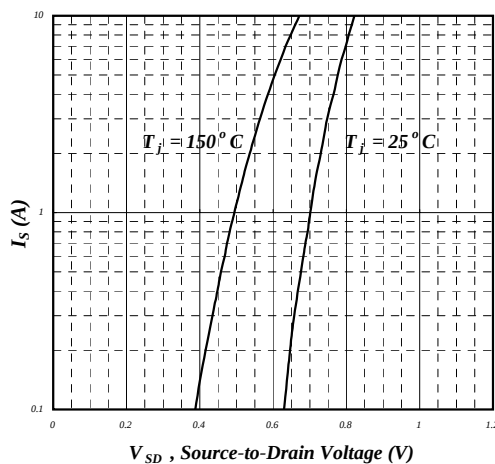


Fig 5. Forward Characteristic of Reverse Diode

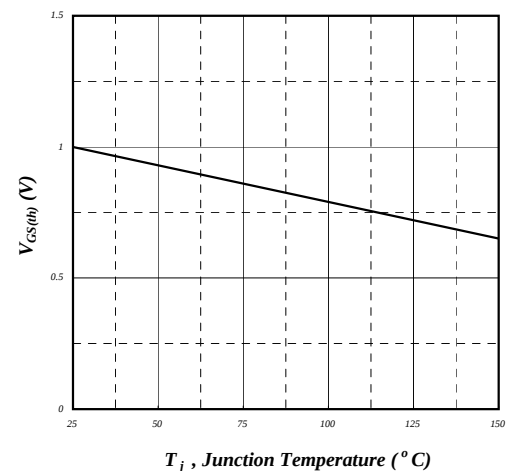


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



AP10N70P/R-A

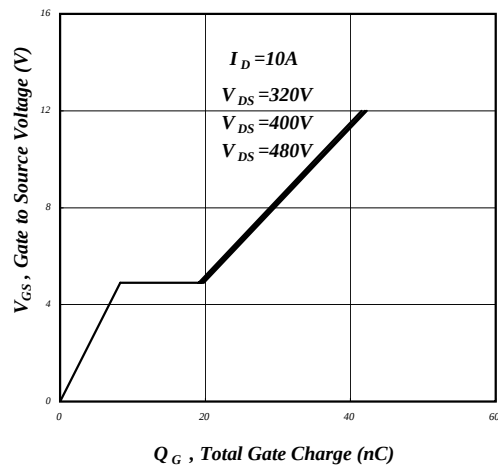


Fig 7. Gate Charge Characteristics

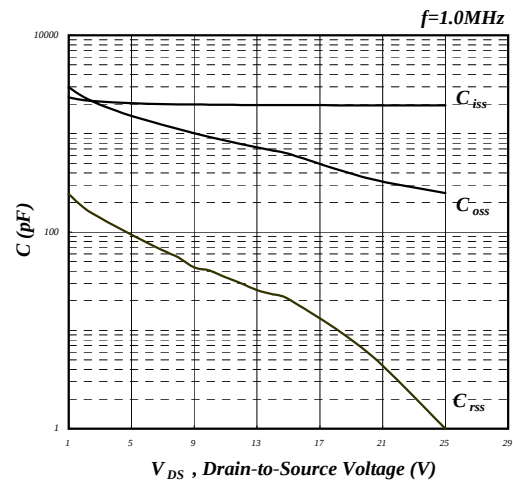


Fig 8. Typical Capacitance Characteristics

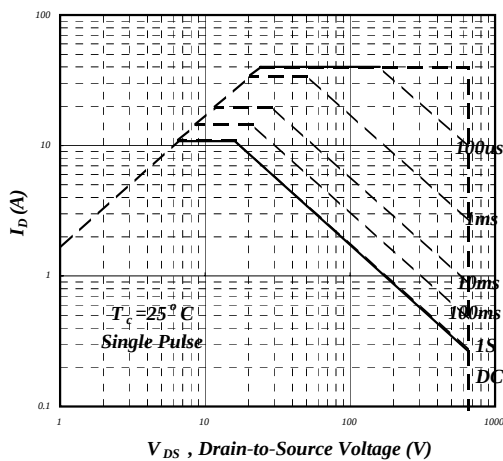


Fig 9. Maximum Safe Operating Area

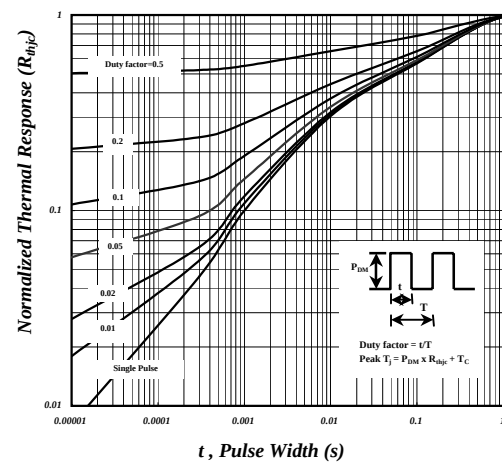


Fig 10. Effective Transient Thermal Impedance

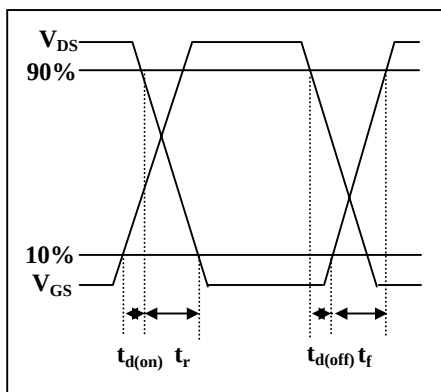


Fig 11. Switching Time Waveform

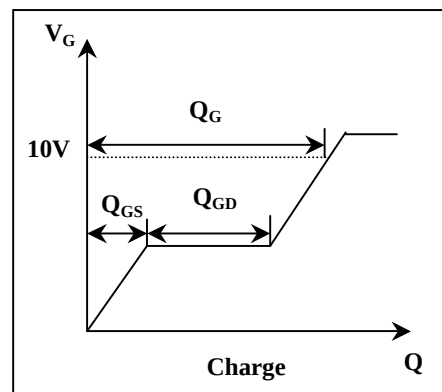


Fig 12. Gate Charge Waveform